

NCE P-Channel Super Trench Power MOSFET

Description

The NCEP40P35GU uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

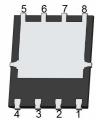
General Features

- V_{DS} =-40V, I_{D} =-35A $R_{DS(ON)}$ =19.0mΩ (typical) @ V_{GS} =-10V $R_{DS(ON)}$ =28.0mΩ (typical) @ V_{GS} =-4.5V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 150 °C operating temperature
- Pb-free lead plating

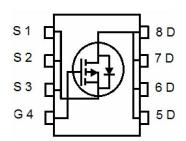
100% UIS TESTED! 100% ΔVds TESTED!

PDFN 5X6-8L





Top View Bottom View



Schematic Diagram

Package Marking and Ordering Information

	Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
	P40P35GU	NCEP40P35GU	PDFN5X6-8L	Ø330mm	12mm	5000units

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	-40	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	-35	Α
Drain Current-Continuous(T _C =100 ℃)	I _D (100℃)	-25	Α
Pulsed Drain Current	I _{DM}	-140	Α
Maximum Power Dissipation	P _D	65	W
Derating factor		0.52	W/°C
Single pulse avalanche energy (Note 1)	Eas	80	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance,Junction-to-Case	R _{θJC}	1.92	°C/W
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NCEP40P35GU

Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250µA	-40		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20 V , V_{DS} =0 V	-	-	±100	nA
On Characteristics			•	•		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=-250\mu A$	-1.0	-1.7	-2.5	V
Drain Sauras On State Registance	В	V _{GS} =-10V, I _D =-15A	-	19.0	26.0	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-15A	-	28.0	38.0	mΩ
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-20A	-	18	-	S
Dynamic Characteristics						
Input Capacitance	Clss	\/ 00\/\/ 0\/	-	1000	-	PF
Output Capacitance	Coss	V _{DS} =-20V,V _{GS} =0V, F=1.0MHz - 315 - 18.5 -	-	PF		
Reverse Transfer Capacitance	Crss		-	18.5	-	PF
Switching Characteristics (Note 2)	·					
Turn-on Delay Time	t _{d(on)}		-	8	-	nS
Turn-on Rise Time	t _r	V_{DD} =-20 V , I_{D} =-15 A	-	10	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10 V , R_{G} =1.6 Ω	-	25	-	nS
Turn-Off Fall Time	t _f		-	6	-	nS
Total Gate Charge	Qg	\/ 00\/ L 45A	-	18.5	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =-20V,I _D =-15A,	-	4.2		nC
Gate-Drain Charge	Q_{gd}	V _{GS} =-10V	-	2.4		nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =-15A	-		-1.2	V
Diode Forward Current	Is		-	-	-35	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =-35A	-	22	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-	25	-	nC

Notes:

- 1. EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=-20V,VG=-10V,L=0.5mH,Rg=25 Ω
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150°C. The SOA curve provides a single pulse rating.



Typical Electrical and Thermal Characteristics

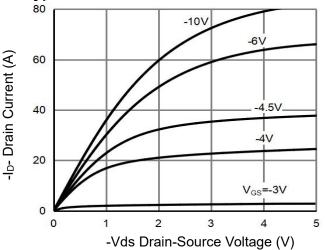


Figure 1 Output Characteristics

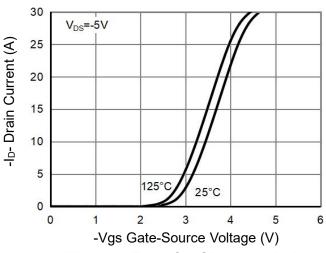


Figure 2 Transfer Characteristics

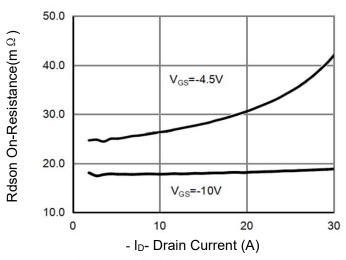


Figure 3 Rdson- Drain Current

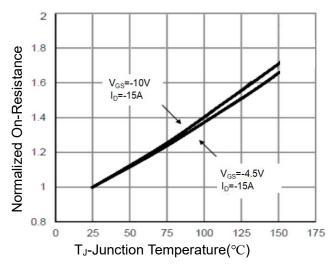


Figure 4 Rdson-JunctionTemperature

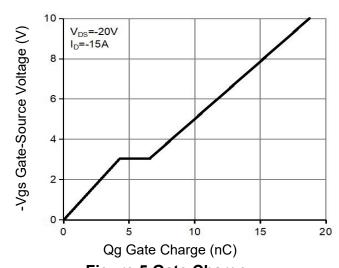


Figure 5 Gate Charge

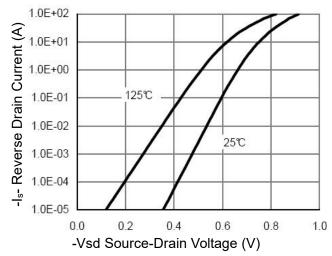


Figure 6 Source- Drain Diode Forward



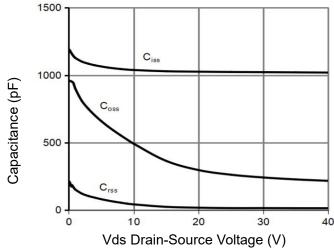


Figure 7 Capacitance vs Vds

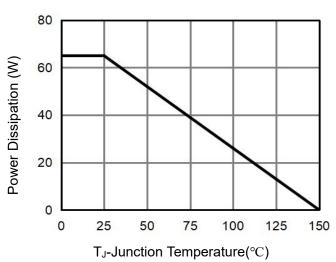


Figure 9 Power De-rating

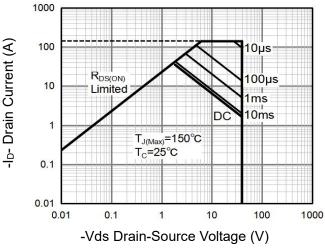


Figure 8 Safe Operation Area(Note3)

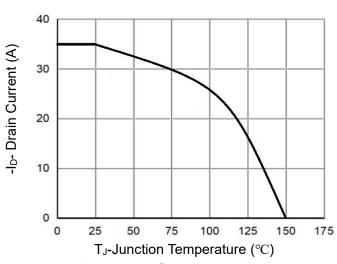


Figure 10 Current De-rating

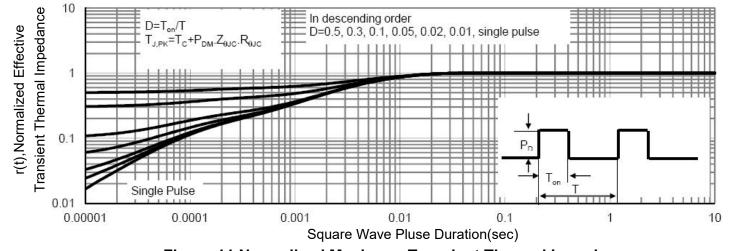
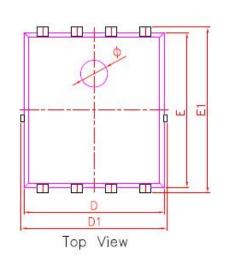
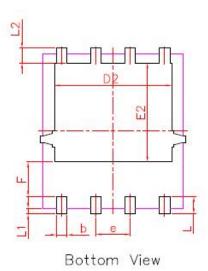


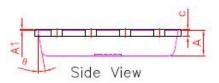
Figure 11 Normalized Maximum Transient Thermal Impedance



PDFN5X6-8L (E)Package Information







DIM.	MIN.	NOM.	MAX.	
Α	0.90	0.95	1.00	
A1	0.00	0.02	0.05	
b	0.35	0.40	0.50	
С	0.20	0.25	0.30	
D	5.10	5.20	5.30	
D1	5.10	5.40	5.50	
D2	4.25 4.35		4.45	
е	1.27 BSC			
Ε	5.70	5.75	5.80	
E1	6.00	6.15	6.30	
E2	3.57	3.67	3.77	
F	1.18	1.28	1.38	
L.	0.55	0.65	0.75	
L1 0.15		0.20	0.25	
L2	0.45	0.55	0.65	
Ø	0.90	1.00	1.10	
Θ	8.	10"	12*	

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NCEP40P35GU

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